

Description

The SX2300MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 4.5A$

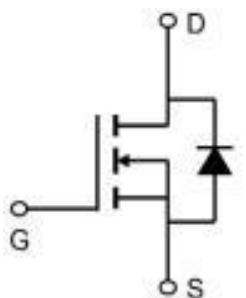
$R_{DS(ON)} < 28m\Omega$ @ $V_{GS}=4.5V$

Application

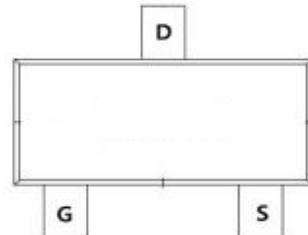
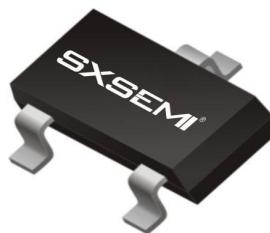
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V ¹	4.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V ¹	2.8	A
I_{DM}	Pulsed Drain Current ²	14.4	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_D=250\mu\text{A}$	20	22	---	V
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=3\text{A}$	---	23	32	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=2.5\text{V}$, $\text{I}_D=2\text{A}$	---	29	35	
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}$, $\text{I}_D=250\mu\text{A}$	0.5	0.75	1.2	V
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=16\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $\text{T}_J=25^\circ\text{C}$	---	---	1	μA
		$\text{V}_{\text{DS}}=16\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $\text{T}_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 12\text{V}$, $\text{V}_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$\text{V}_{\text{DS}}=5\text{V}$, $\text{I}_D=3\text{A}$	---	10.5	---	S
Q_{g}	Total Gate Charge (4.5V)	$\text{V}_{\text{DS}}=15\text{V}$, $\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=3\text{A}$	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	0.7	---	
Q_{gd}	Gate-Drain Charge		---	1.5	---	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{DD}}=10\text{V}$, $\text{V}_{\text{GS}}=4.5\text{V}$, $\text{R}_G=3.3\Omega$ $\text{I}_B=3\text{A}$	---	1.6	---	ns
T_r	Rise Time		---	42	---	
$\text{T}_{\text{d(off)}}$	Turn-Off Delay Time		---	14	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	$\text{V}_{\text{DS}}=15\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	310	---	pF
C_{oss}	Output Capacitance		---	49	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	
I_{s}	Continuous Source Current ^{1,4}	$\text{V}_{\text{G}}=\text{V}_{\text{D}}=0\text{V}$, Force Current	---	---	3.6	A
V_{SD}	Diode Forward Voltage ²	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_{\text{s}}=1\text{A}$, $\text{T}_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

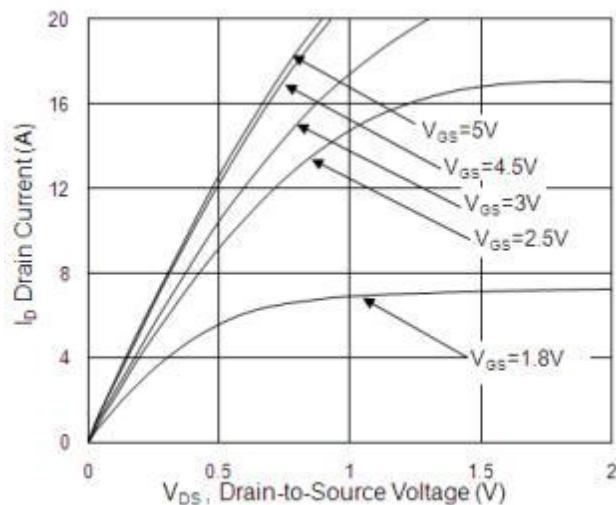


Fig.1 Typical Output Characteristics

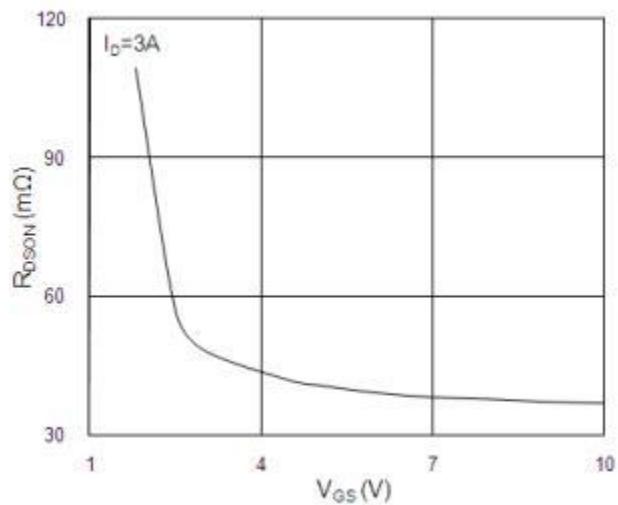


Fig.2 On-Resistance vs. G-S Voltage

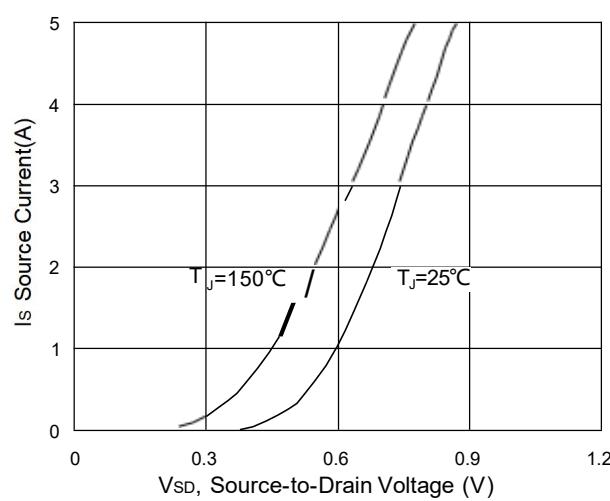


Fig.3 Source Drain Forward Characteristics

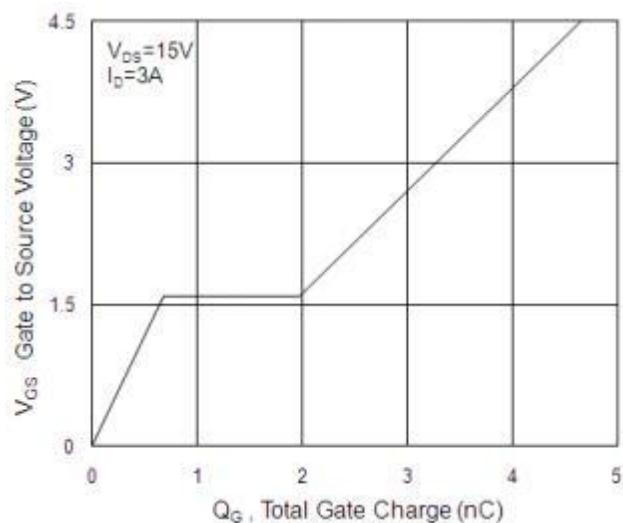


Fig.4 Gate-Charge Characteristics

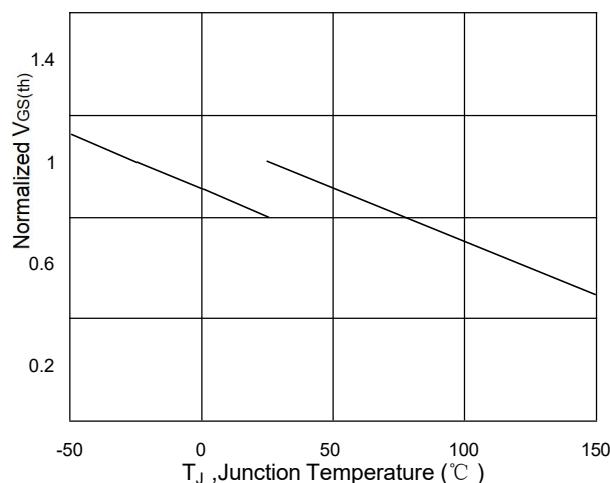


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

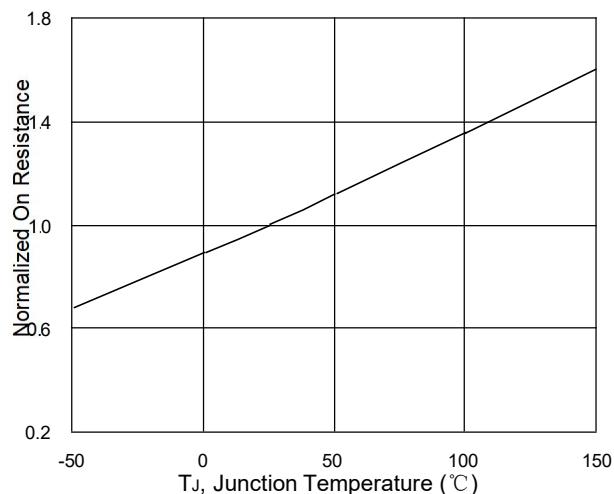


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

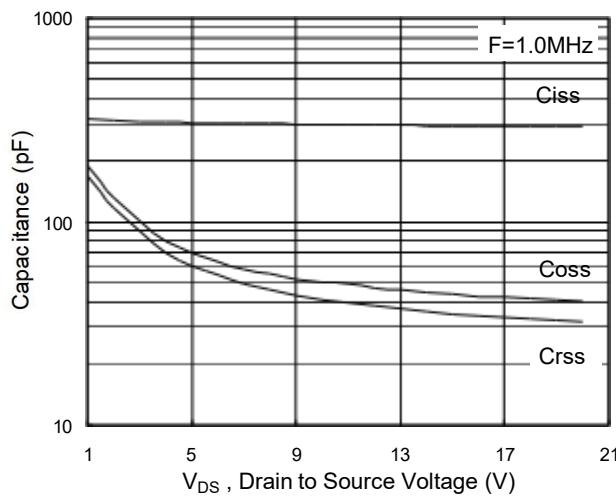


Fig.7 Capacitance

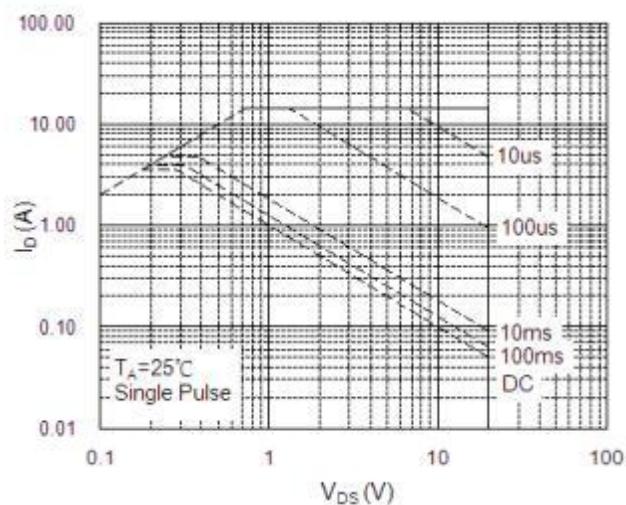


Fig.8 Safe Operating Area

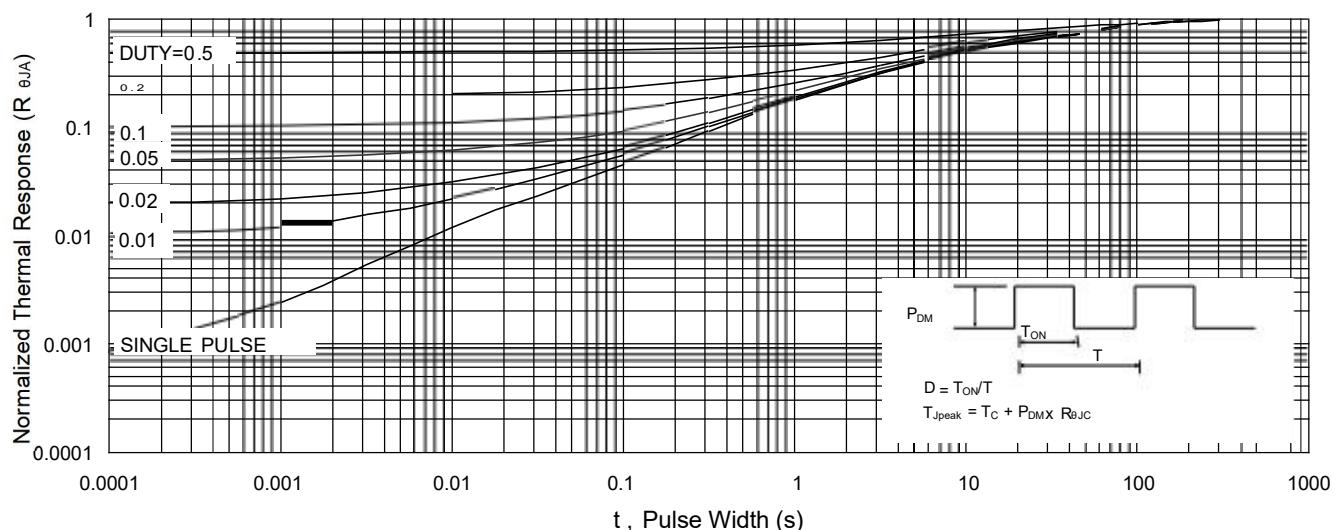


Fig.9 Normalized Maximum Transient Thermal Impedance

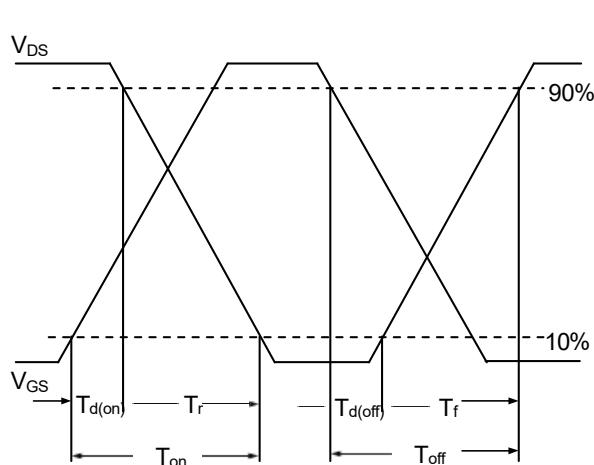


Fig.10 Switching Time Waveform

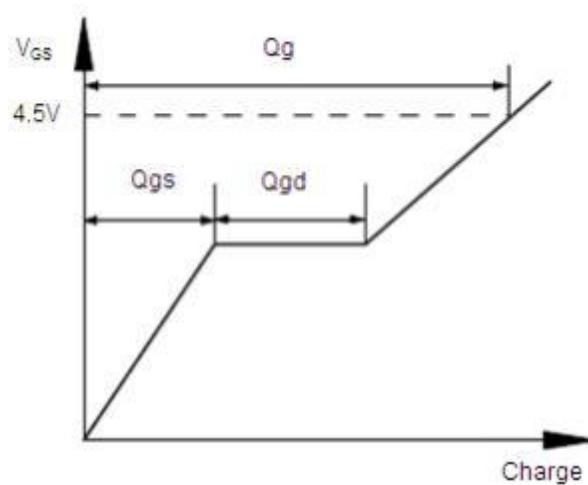
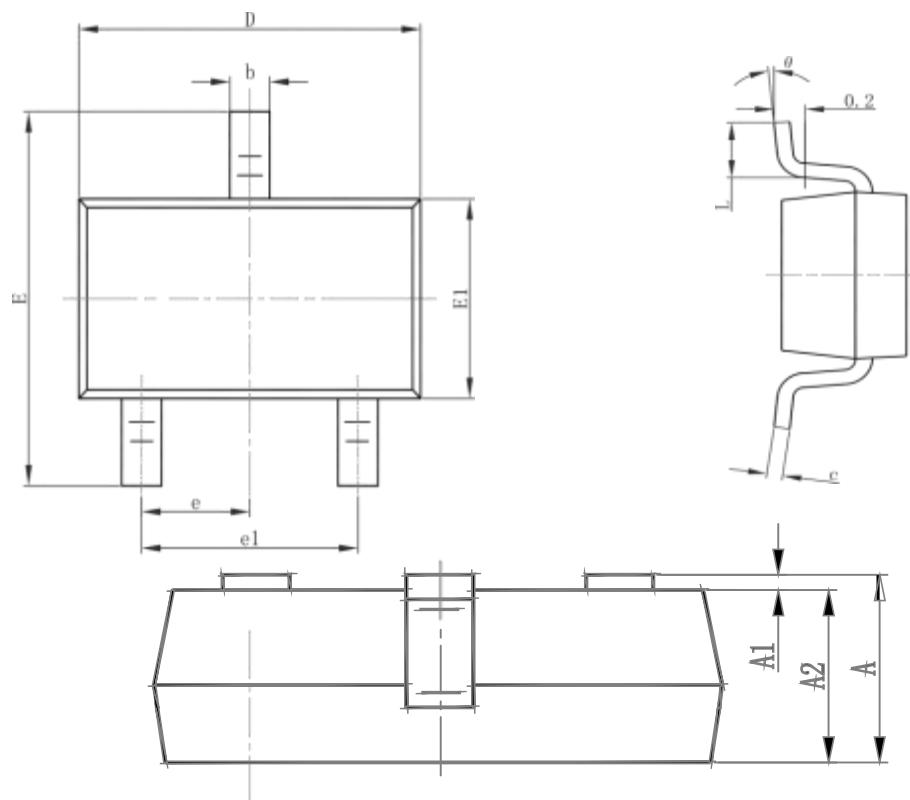


Fig.11 Gate Charge Waveform

MOSFET Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT-23-3L		3000